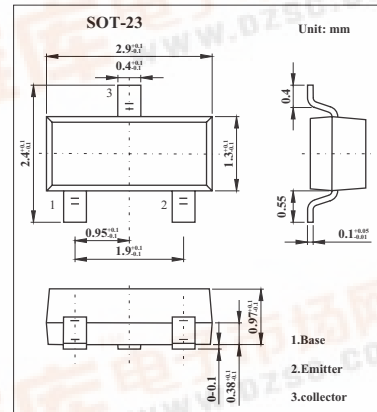
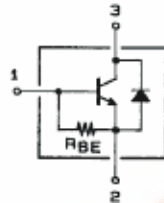


SMD Type Transistors

NPN Epitaxial Planar Silicon Transistor
2SD2324

■ Features

- Low saturation voltage.
- Contains a diode between collector and emitter.
- Contains a bias resistor between base and emitter.
- Large current capacity.
- Small-sized package facilitating the realization of high-density, small-sized hybrid ICs.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage, With Zener diode (11±3V)	V _{CB0}	20	V
Collector-emitter voltage, With Zener diode (11±3V)	V _{CEO}	15	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _c	0.8	A
Collector current (pulse)	I _{CP}	2	A
Collector dissipation	P _c	200	mW
Jumction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{cBO}	V _{CB} = 15V, I _E = 0			1.0	μA
DC current Gain	h _{FE}	V _{CE} = 2V, I _C = 0.5A	70			
Gain bandwidth product	f _T	V _{CE} = 2V, I _C = 0.5A		150		MHz
Output capacitance	C _{ob}	V _{CB} = 10V, f = 1MHz		15		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 500mA, I _B = 10mA		0.16	0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 500mA, I _B = 10mA		0.85	1.2	V
Collector-to-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	20			V
Collector-to-emitter breakdown voltage	V _{(BR)CEO}	I _C = 10μA, R _{BE} = ∞	20			V
		I _C = 10mA, R _{BE} = ∞	15			
Diode forward voltage	V _F	I _F = 0.5A			1.5	V
Base-emitter resistance	R _{BE}			1		kΩ

■ Marking

Marking	BN
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